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May 2024

FAN7621B PFM Controller for Half-Bridge Resonant Converters

Features

- Variable Frequency Control with 50% Duty Cycle for Half-bridge Resonant Converter Topology
- High Efficiency through Zero Voltage Switching (ZVS)
- Fixed Dead Time (350ns)
- Up to 300kHz Operating Frequency
- Pulse Skipping for Frequency Limit (Programmable) at Light-Load Condition
- Remote On/Off Control using CON Pin
- Protection Functions: Over-Voltage Protection (OVP), Overload Protection (OLP), Over-Current Protection (OCP), Abnormal Over-Current Prote Joi (AOCP), Internal Thermal Shutdown (TSD)

Applications

- PDP and LCD TVs
- Desktop PCs and Ser
- Adapters
- Telecom Po
- Video Gan Co

Description

The FAN7621B is a pulse fr ency modulation controller for high-efficiency nalt-, dge resonant converters. Offering everything necess by to build a reliable and robust reso ant con rter he FAN7621B simplifies designs at im loves oductivity, while improving perform. ce. a FAN 621B includes a highside gate-dri e circ a. a arate current controlled oscillator free ency it c.cuit, soft-start, and built-in protection incomes. To high-side gate-drive circuit has non ode use cancellation capability, which able operation with excellent noise iar, tec Using the zero-voltage-switching (ZVS) ii huri tec liqu dramatically reduces the switching losses and efficincy is significantly improved. The ZVS also reduces (ne switching ic se noticeably, which allows a small-pized Electromagnetic Interference (EMI) filter.

The FAN76212 can be applied to various resonant converter topologies; such as series resonant, parallel rescriant, and LLC resonant converters.

Related Resources

Half-bridge LLC Resonant Converter Design series Fairchild Power Switch (FPS^TM)

.g Information

Part Number	Operating Junction Temperature	Package	Packaging Method
FAN7621BSJ	-40°C ~ 130°C	16-Lead Small Outline Package (SOP)	Tube
FAN7621BSJX	-40°C ~ 130°C	10-Lead Small Oddille Package (SOP)	Tape & Reel

Application Circuit Diagram

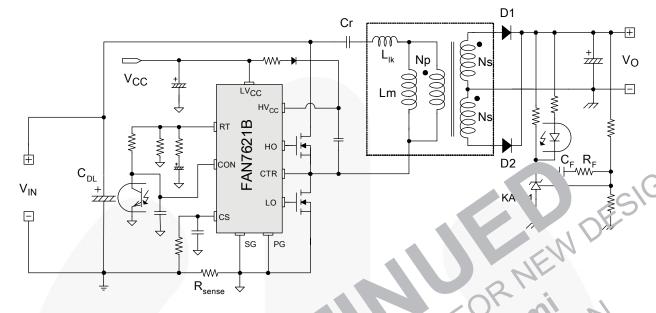
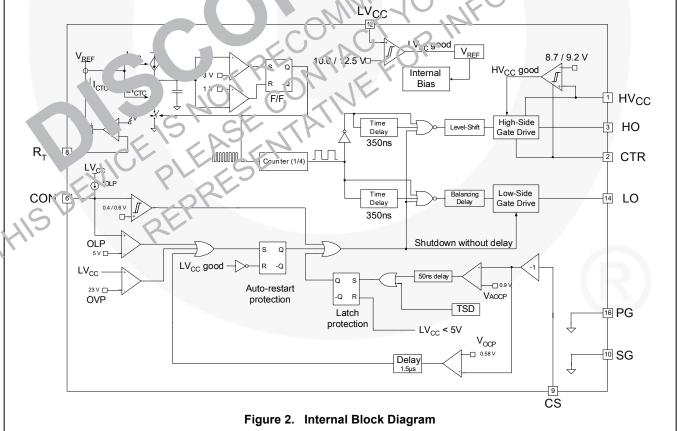


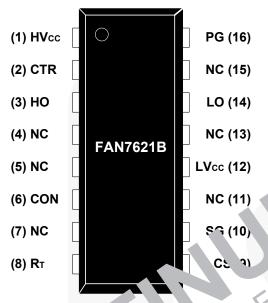
Figure 1. Typical Application Cir (LLC 'es ant Half-Bridge Convertor)

Block Diagram



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Pin Configuration



ckage liag m Figure 3

Pin Definitions

			(4) NC				
			(6) CON NC (11)				
			(6) CON [
			(8) R _T Ct 2)				
Pir	n Defi	nitions	Figure 3 vckage Viag vm				
Р	Pin #	Name	Description				
	1	HV _{cc}	This is to supply oltage of the high-side gate-drive circuit IC.				
	2	CTR	his is the of the low-side MOSFET. Typically, a transformer is connected to this pin.				
	3	μ	This is to supply oblige of the high-side gate-drive circuit IC. This is the connected to this pin. This is the low-side MOGFET. Typically, a transformer is connected to this pin. This is the high-side gate driving signal.				
	4	_ NC	Nnection.				
	5	NC	No connection.				
	q	CON	This pin is for a protection and enabling/disabling the controller. When the voltage of this pin is above 0.6%, the IC operation is enabled. When the voltage of this pin drops below 0.4V, gate drive signals for both MOSFETs are disabled. When the voltage of this pin increases above 5V, protection is triggered.				
	7	NC	No connection				
	8	R⊤	This programs the switching frequency. Typically, an opto-coupler is connected to cont of the switching frequency for the output voltage regulation.				
	9	cs	This pin senses the current flowing through the low-side MOSFET. Typically, negative voltage is applied on this pin.				
	10	SG	This pin is the control ground.				
	11	NC	No connection.				
	12	LV _{CC}	This pin is the supply voltage of the control IC.				
	13	NC	No connection.				
	14	LO	This is the low-side gate driving signal.				
	15	NC	No connection.				
	16	PG	This pin is the power ground. This pin is connected to the source of the low-side MOSFET.				

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. $T_A=25^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Min.	Max.	Unit
V_{HO}	High-Side Gate Driving Voltage	V _{CTR} -0.3	HV _{CC}	V
V_{LO}	Low-Side Gate Driving Voltage	-0.3	LV _{CC}	V
LV _{CC}	Low-Side Supply Voltage	-0.3	25.0	V
HV _{CC} to V _{CTR}	High-Side V _{CC} Pin to Center Voltage	-0.3	25.0	V
V _{CTR}	Center Voltage	-0.3	J.	V
V _{CON}	Control Pin Input Voltage	-0.3	LV _{CC}	V
V _{CS}	Current Sense (CS) Pin Input Voltage	_F	0	V
V _{RT}	R _T Pin Input Voltage	-O.	5.0	V
dV _{CTR} /dt	Allowable Center Voltage Slew Rate		50	V/ns
P _D	Total Power Dissipation 16-SOP		1.13	W
_	Maximum Junction Temperature ⁽¹⁾		+150	00
T_J	Recommended Operating Junction Temp at (1)	-40	4.(20)	°C
T _{STG}	Storage Temperature Range	-55	+150	°C

Note:

Thermal Impedang

Symbol	Parameter	Value	Unit
θ_{JA}	J Anibient Ther mal Impedance 16-SOP	110	°C/W

^{1.} The maximum value of the recommend operating junction temperature is limited by the mail shutdown.

Electrical Characteristics

 $T_A \! = \! 25^{\circ} C$ and LV $_{CC} \! = \! 17V$ unless otherwise specified.

Symbol	Parameter Test Conditions		Min.	Тур.	Max.	Unit
Supply Sect	ion					
I _{LK}	Offset Supply Leakage Current	HV _{CC} =V _{CTR}			50	μA
I_QHV_{CC}	Quiescent HV _{cc} Supply Current	(HV _{CC} UV+) - 0.1V		50	120	μA
I _Q LV _{CC}	Quiescent LV _{cc} Supply Current	(LV _{CC} UV+) - 0.1V		100	200	μA
I_0HV_{CC}	Operating HV _{cc} Supply Current (RMS Value)	$\begin{array}{l} f_{OSC} {=} 100 kHz, V_{CON} > 0.6V,\\ C_{Load} {=} 1nF \end{array}$		5	8	mA
	(Nivio Value)	No Switching, V _{CON} < 0.4V		JU	200	μΑ
I _o LV _{cc}	Operating LV _{cc} Supply Current (RMS Value)	f_{OSC} =100kHz, V_{CON} > 0.6V, C_{Load} =1nF		િ	9	ınΛ
	(rivie value)	No Switching, V _{CON} < 0.4		2	4	mA
UVLO Section	on				11	
LV _{CC} UV+	LV _{CC} Supply Under-Voltage Positive C	Going Threshold (L 2 S 1)	11.2	12.5	13.8	V
LV _{CC} UV-	LV _{CC} Supply Under-Voltage Negative	Going Tresi Stop)	3.90	10.00	11.10	V
LV _{CC} UVH	LV _{CC} Supply Under-Voltage Hysteresi	S		2.5	10.	V
HV _{CC} UV+	HV _{CC} Supply Under-Voltage Positine	Goin, Thresh 1 (HVc; Start)	8.2	9.2	10.2	V
HV _{CC} UV-	HV _{cc} Supply Under-Voltage * ¬ativ	Going reshold (HV _{3c} Stop)	7.8	87	9.6	V
HVccUVH	HV _{CC} Supply Under-\(\sigma \) H, 'ere-		0.5		V	
Oscillator &	Feedback Section	1/1/1/1/10/14	70			
V _{CONDIS}	Control Pi Jisable ash J Voltage	0, 51	0.36	0.40	0.44	V
V _{CONEN}	Control P Enable Threshold Voitage			0.60	0.66	V
V _{RT}	-I Comprte. Ushold Voltage	MICH	1.5	2.0	2.5	V
fosc	Output C sillation Frequency R ₁ =5 2kΩ			100	106	kHz
DC	utput Duty Cycle		48	50	52	%
f _{SS}	Internal Soft-Start Initial Frequency	$f_{SS}=f_{OSC}+40kHz, R_T=5.2k\Omega$	7	140		kHz
	Internal Soft Start Time		2	3	4	ms
Output Sect	ion					
I _{source}	Peak Sourcing Current	HV _{CC} =17V	250	360		mA
I _{sink}	Peak Sir king Current	HV _{CC} =17V	460	600		mA
tr	Rising Time	0 4.5.107 4777		65		ns
t_f	Falling Time	C _{Load} =1nF, HV _{CC} =17V		35		ns
V _{HOH}	High Level of High-Side Gate Driving Signal (VHVCC-VHO)				1.0	V
V_{HOL}	Low Level of High-Side Gate Driving Signal	I=-20mA			0.6	V
V_{LOH}	High Level of High-Side Gate Driving Signal (V _{LVCC} -V _{LO})				1.0	V
V_{LOL}	Low Level of High-Side Gate Driving Signal				0.6	٧

Electrical Characteristics (Continued)

T_A=25°C and LV_{CC}=17V unless otherwise specified.

	Parameter	Test Conditions	Min.	Тур.	Max.	
Protection	Section					
I _{OLP}	OLP Delay Current	V _{CON} =4V	3.8	5.0	6.2	
V_{OLP}	OLP Protection Voltage	V _{CON} > 3.5V	4.5	5.0	5.5	
V _{OVP}	LV_{CC} Over-Voltage Protection $LV_{CC} > 21V$ 21				25	
V _{AOCP}	AOCP Threshold Voltage		-1.0	-0.9	-0.8	
t _{BAO}	AOCP Blanking Time			-		
V_{OCP}	OCP Threshold Voltage		-0.64	0.58	0.52	
t_{BO}	OCP Blanking Time ⁽²⁾		1.0	-	2.0	
t _{DA}	Delay Time (Low-Side) Detecting from V_{AOCP} to Switch $\text{Off}^{(2)}$			_50	400	
T _{SD}	Thermal Shutdown Temperature ⁽²⁾		110	130	150	
I _{SU}	Protection Latch Sustain LV _{CC} Supply Current	LV _{CC} - 5V	OP	100	150	
V_{PRSET}	Protection Latch Reset LV _{CC} Supply Voltage	CD	5	SI,	10	
Dead-Time	Control Section	NO	0,	NP		
D _T	Dead Time	NE OUT		350		
2. These pa	arameters, alther high rantee are not the	teસ્પરુહ in production.	7,			
2. These pa	arameters, alther high rantee are not to	texteu in production.	7,			

Typical Performance Characteristics

These characteristic graphs are normalized at T_A=25°C.

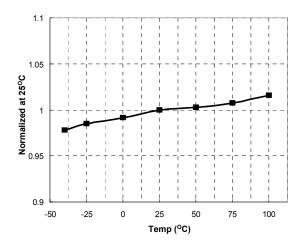


Figure 4. Low-Side MOSFET Duty Cycle vs. Temperature

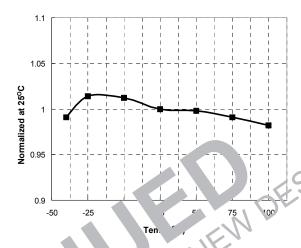
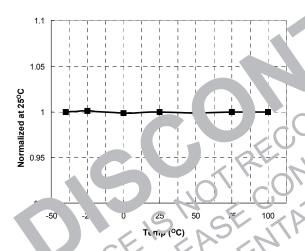


Figure & Sw. hir Frequency vs. Temperature



Figur .. High-Side V_{cc} (HV_{cc}) Start vs. Temperature

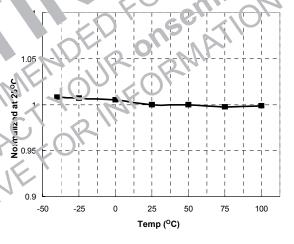


Figure 7. High-Side V_{CC} (HV_{CC}) Stop vs. Temperature

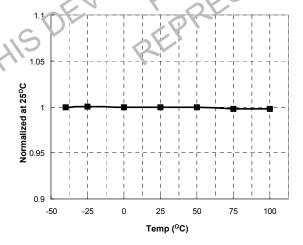


Figure 8. Low-Side V_{CC} (LV_{CC}) Start vs. Temperature

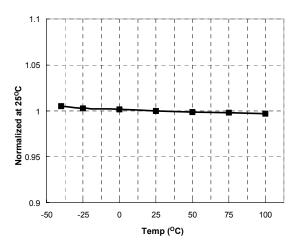
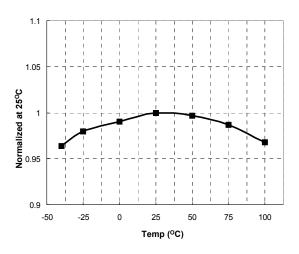


Figure 9. Low-Side V_{CC} (LV_{CC}) Stop vs. Temperature

Typical Performance Characteristics (Continued)

These characteristic graphs are normalized at T_A=25°C.



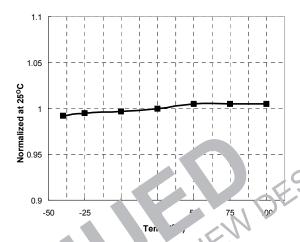
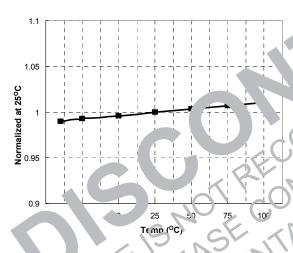
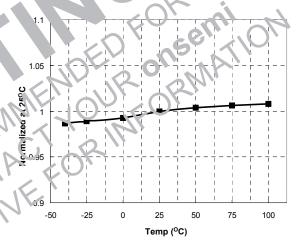


Figure 10. OLP Delay Current vs. Temperature

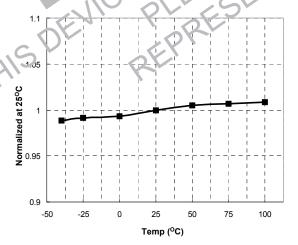
Figure 1: 7LF 'rot' stion Voltage vs. Temperature





qu' 12. LYcc OVP Voltage vs. Temperature

Figure 13. R_T Voltage vs. Temperature



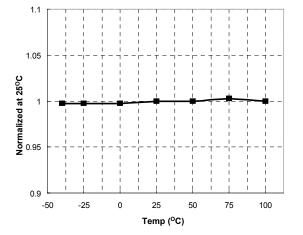


Figure 14. CON Pin Enable Voltage vs. Temperature

Figure 15. OCP Voltage vs. Temperature

Functional Description

1. Basic Operation: FAN7621B is designed to drive high-side and low-side MOSFETs complementarily with 50% duty cycle. A fixed dead time of 350ns is introduced between consecutive transitions, as shown in Figure 16.

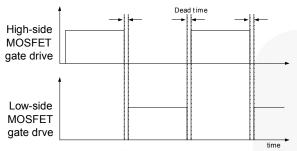
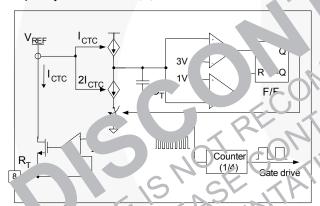


Figure 16. MOSFETs Gate Drive Signal

2. Internal Oscillator: FAN7621B employs a current-controlled oscillator, as shown in Figure 17. Internally, the voltage of R_T pin is regulated at 2V and the charging / discharging current for the oscillator capacitor, C_T , is obtained by copying the current flowing out of R_T pin (I_{CTC}) using a current mirror. Therefore, the switchir frequency increases as I_{CTC} increases.



√ure 17. Culvent Con'rolled Oscillator

3. Frequency Setting: Figure 18 shows the typical voltage gain curve of a resonant converter, where the gain is inversely proportional to the switching frequency in the ZVS region. The output voltage can be regulated by modulating the switching frequency. Figure 19 shows the typical circuit configuration for R_T pin, where the opto-coupler transistor is connected to the R_T pin to modulate the switching frequency.

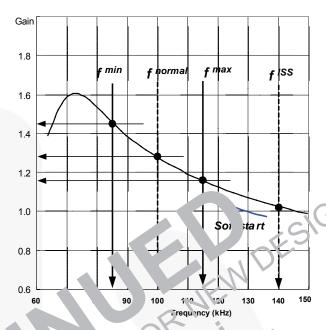


Fig. ຈາຍ. sonant Corverter Tາກາເລl Gain Curve

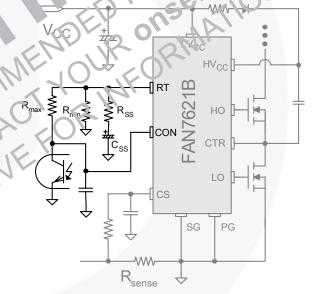


Figure 19. Frequency Control Circuit

The minimum switching frequency is determined as:

$$f^{\min} = \frac{5.2k\Omega}{R_{\min}} \times 100(kHz) \tag{1}$$

Assuming the saturation voltage of opto-coupler transistor is 0.2V, the maximum switching frequency is determined as:

$$f^{\max} = (\frac{5.2k\Omega}{R_{\min}} + \frac{4.68k\Omega}{R_{\max}}) \times 100 (kHz)$$
 (2)

To prevent excessive inrush current and overshoot of output voltage during startup, increase the voltage gain of the resonant converter progressively. Since the voltage gain of the resonant converter is inversely

proportional to the switching frequency, the soft-start is implemented by sweeping down the switching frequency from an initial high frequency (f^{ISS}) until the output voltage is established. The soft-start circuit is made by connecting R-C series network on the R_T pin, as shown in Figure 19. FAN7621B also has an internal soft-start for 3ms to reduce the current overshoot during the initial cycles, which adds 40kHz to the initial frequency of the external soft-start circuit, as shown in Figure 20. The initial frequency of the soft-start is given as:

$$f^{ISS} = (\frac{5.2k\Omega}{R_{\min}} + \frac{5.2k\Omega}{R_{SS}}) \times 100 + 40 \ (kHz)$$
 (3)

It is typical to set the initial (soft-start) frequency of two \sim three times the resonant frequency (f_O) of the resonant network.

The soft-start time is three to four times the RC time constant. The RC time constant is as follows:

$$T_{SS} = R_{SS} \cdot C_{SS} \tag{4}$$

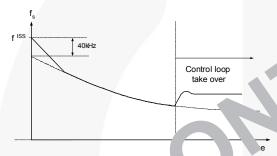


Figure 20. Frequency Jep. 7 of \$ t-Start

4. Control Pin: The F. V7621P has a control pin for protection, cycle ... ping and renote on of a Figure 21 shows the internal block diagram or control pin.

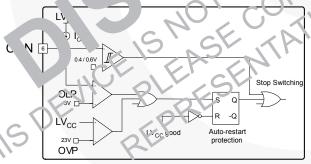


Figure 21. Internal Block of Control Pin

Protection: When the control pin voltage exceeds 5V, protection is triggered. Detailed applications are described in the protection section.

Pulse Skipping: FAN7621B stops switching when the control pin voltage drops below 0.4V and resumes switching when the control pin voltage rises above 0.6V. To use pulse-skipping, the control pin should be connected to the opto-coupler collector pin. The frequency that causes pulse skipping is given as:

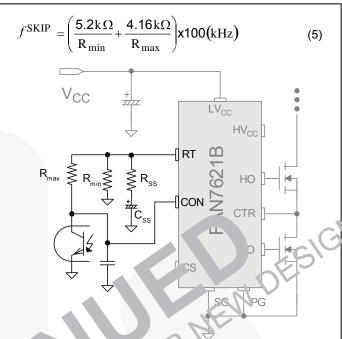


Figure 22. Control Pin Configuration for Pulse Skipping

Remote On / On: When an auxiliary power supply is used for standby, the main power stage using FAN70213 can be snot down by pulling down the control provoltage as shown in Figure 23. R1 and C1 are used to ensure soft-start when switching resumes.

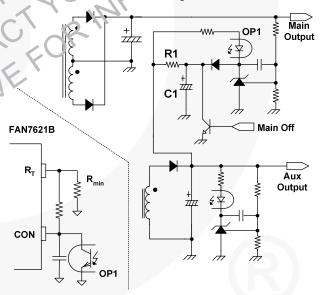


Figure 23. Remote On / Off Circuit

5. Protection Circuits: The FAN7621B has several self-protective functions, such as Overload Protection (OLP), Over-Current Protection (OCP), Abnormal Over-Current Protection (AOCP), Over-Voltage Protection (OVP), and Thermal Shutdown (TSD). OLP, OCP, and OVP are auto-restart mode protections; while AOCP and TSD are latch-mode protections, as shown in Figure 24.

Auto-Restart Mode Protection: Once a fault condition is detected, switching is terminated and the MOSFETs remain off. When LV_{CC} falls to the LV_{CC} stop voltage of 10.0V, the protection is reset. FAN7621B resumes normal operation when LV_{CC} reaches the start voltage of 12.5V.

Latch-Mode Protection: Once this protection is triggered, switching is terminated and the gate output signals remain off. The latch is reset only when LV_{CC} is discharged below 5V.

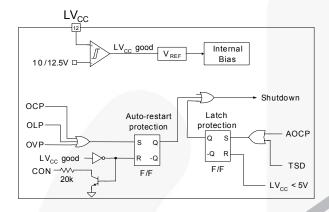


Figure 24. Protection Blocks

Current Sensing Using Resistor: FAN7621B the sensing current as a negative voltage, as showing Filipse 25 and Figure 26. Half-wave sensing resistor, the fill-wave sensing has less switching noise in the sensing signal.

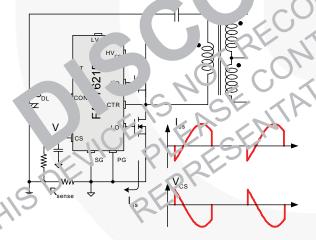


Figure 25. Half-Wave Sensing

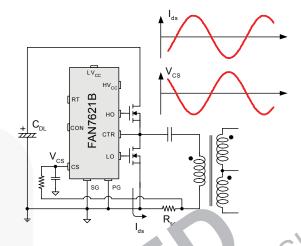
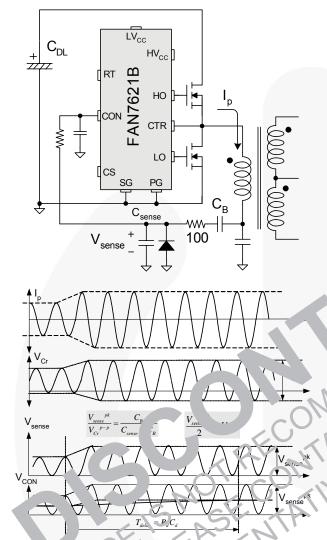


Figure 26. Figure 36. Figure 26. Figure 36. Figure 36.

Current Sensing ''sin, '' sonant spacifor /oitage: For high-power aptications, when the sensing using a resistor may be all a due to the severe power dissipation in the resistor. In that case, indirect current senting using a transfer of the severe power dissipation in the resistor. In that case, indirect current senting using a transfer of the resonant capacitor voltage can be a cool of the resonant capacitor voltage ($V_{\rm p}^{\rm pp}$) is proportion at to the resonant current the primary side ($I_{\rm p}^{\rm pp}$) as.

$$V_{Cr}^{p-p} = \frac{I_{2}}{2\pi} \frac{I_{2}}{I_{C}}$$
 (6)

To minimize power dissipation, a capacitive voltage divider is generally used for capacitor voltage sensing, as shown in Figure 27.



ure 27. Current Seasing Using Resonant Capacitor Voltage

5.1 Over Current Protection (OCP): When the sensing pin voltage drops below -C.6V, OCP is triggered and the MOSFETs remain off. This protection has a shutdown time delay of 1.5µs to prevent premature shutdown during startup.

5.2 Abnormal Over-Current Protection: **(AOCP)**: If the secondary rectifier diodes are shorted, large current with extremely high di/dt can flow through the MOSFET before OCP or OLP is triggered. AOCP is triggered without shutdown delay when the sensing pin voltage drops below -0.9V. This protection is latch mode and reset when LV_{CC} is pulled down below 5V.

5.3 Overload Protection (OLP): Overload is defined as the load current exceeding its normal level due to an unexpected abnormal event. In this situation, the protection circuit should trigger to protect the power supply. However, even when the power supply is in the normal condition, the overload situation can occur during the load transition. To avoid produre triggering of protection, the overload prot ion coult should be designed to trigger only after a sprified time to determine whether it is a transic 'sity tion or a true overload situation. Fig. 9.21 show . typicai cverload protection circuit. v s sing the resonant capacitor voltage on the controllin, a serioad protection can be implemented. 'sing it in a constant, shutdown delay can be a n in nduc . The voltage obtained on the avir , nir COI.

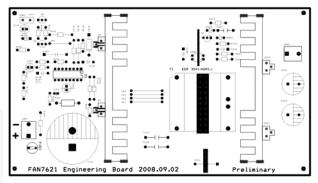
$$V_{c} = \frac{c_{B}}{c_{B} + C_{c}} V_{C_{c}} - V_{C_{c}}$$
 (7)

where $V_{C_1}^{(n)}$ is the amplitude of the resonant capacitor voltage.

- 5.4 Over-Voltage Protection: (OVP): When the LV $_{CC}$ reaches 25V, DVP is triggered. This protection is used when auxiliary winding of the transformer to supply V $_{CC}$ to the controller is utilized.
- **5.5 The mal Shutdown (TSD)**: If the temperature of the junction exceeds approximately 130°C, the thermal shutdown triggers.

6. PCB Layout Guideline: Duty imbalance problems may occur due to the radiated noise from main transformer, the inequality of the secondary-side leakage inductances of main transformer, and so on. Among them, it is one of the dominant reasons that the control components in the vicinity of R_T pin are enclosed by the primary current flow pattern on PCB layout. The direction of the magnetic field on the components caused by the primary current flow is changed when the high-and-low side MOSFET turns on by turns. The magnetic fields with opposite direction from each other induce a current through, into, or out of the R_T pin, which makes the turnon duration of each MOSFET different. It is strongly recommended to separate the control components in the vicinity of R_T pin from the primary current flow pattern on PCB layout. Figure 28 shows an example for the dutybalanced case. The yellow and blue lines show the primary current flows when the lower-side and higherside MOSFETs turns on, respectively. The primary current does not enclose any component of controller.

In addition, it is helpful to reduce the duty imbalance to make the loop configured between CON pin and optocoupler as small as possible, as shown in the red line in Figure 28.



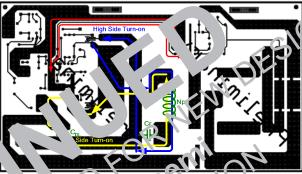


Figure 28. Example for Duty Ealancing

Typical Application Circuit (Half-Bridge LLC Resonant Converter)

Application	Device	Input Voltage Range	Rated Output Power	Output Voltage (Rated Current)
LCD TV	FAN7621B	390V _{DC} (340~400V _{DC})	192W	24V-8A

Features

- High efficiency (>94% at 400V_{DC} input)
- Reduced EMI noise through zero-voltage-switching (ZVS)
- Enhanced system reliability with various protection functions

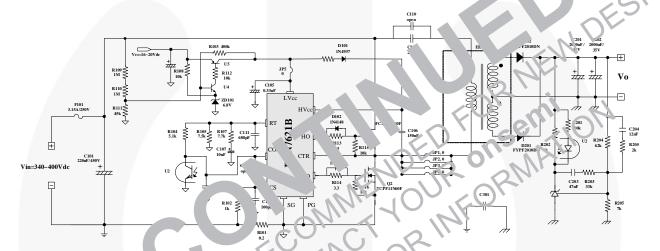


Figure 29. Typical Application Circuit

Typical Application Circuit (Continued)

Usually, LLC resonant converters require large leakage inductance value. To obtain a large leakage inductance, sectional winding method is used.

Core: EC35 (Ae=106 mm²)
 Bobbin: EC35 (Horizontal)

Transformer Model Number: SNX-2468-1

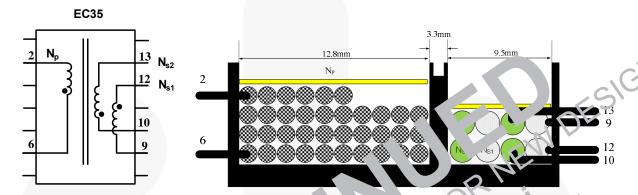
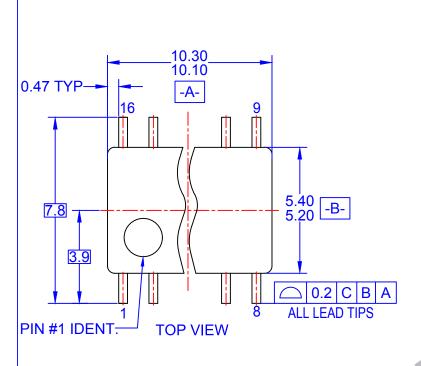


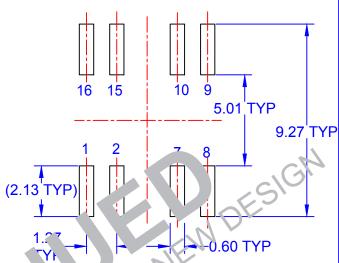
Figure 30. Transorme Son Sruction

	Pins (S → F)	W. Turns	Note
N _p	6 → 2	784 88 (Li∠ Wire) 35	
N _{s1}	12 → 9	0.(p×234 (Litz Wire) 4	Bifilar Winding
N _{s2}	10 → 1	∪.08φ×234 (Litz Wire) 4	Bifilar Winding

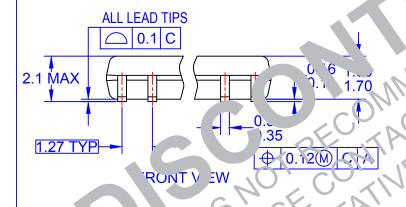
Pins	Specifications	Remark
Prii. γ-、'e Inuuctance (L _p) 2 – 6	550μH ± 10%	100kHz, 1V
P. rary- de Effective Leakage () 2 -0	110μH ± 10%	Short one of the secondary windings

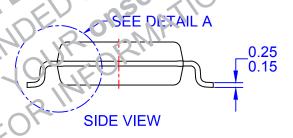
For more detailed information regarding the transformer, visit http://www.santronics-usa.com/documents.html or contact sales @santronics-usa.com or +1-408-734-1878 (Sunnyvale, California USA).

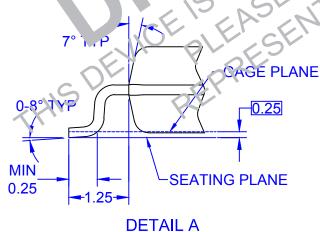




TERN RECOMMENDATION







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